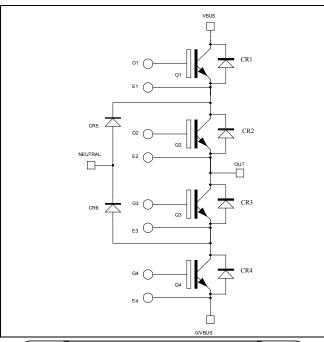


Three level inverter Trench + Field Stop IGBT4 Power Module





Application

- Solar converter
- Uninterruptible Power Supplies

Features

- Trench + Field Stop IGBT 4 Technology
 - Low voltage drop
 - Low leakage current
 - Low switching losses
 - Soft recovery parallel diodes
 - Low diode VF
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

Q1 to Q4 Absolute maximum ratings

X X				
Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		1200	V
Ţ	Continuous Collector Current	$T_c = 25^{\circ}C$	305	
I_{C}	Continuous Collector Current	$T_c = 80^{\circ}C$	240	A
I_{CM}	Pulsed Collector Current	$T_c = 25$ °C	400	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Maximum Power Dissipation	$T_c = 25$ °C	1000	W
RBSOA	Reverse Bias Safe Operating Area	$T_i = 150^{\circ}C$	400A @ 1150V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Q1 to Q4 Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V ; V_{CE} = 1200V$				2	mA
V _{CE(sat)}	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $I_{C} = 200A$	$T_j = 25^{\circ}C$ $T_i = 150^{\circ}C$		1.8	2.2	V
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 5 \text{ mA}$		5	5.8	6.5	V

Q1 to Q4 Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$			12.3		
C_{oes}	Output Capacitance				0.8		nF
Cres	Reverse Transfer Capacitance	f = 1MHz			0.69		
Q_{G}	Gate charge	$V_{GE}=\pm 15V$			1.7		μC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)			160		
T_{r}	Rise Time	$V_{GE} = \pm 15V$			30		ns
T _{d(off)}	Turn-off Delay Time	$V_{CE} = 600V$ $I_{C} = 200A$			340		
$T_{\rm f}$	Fall Time	$R_G = 3.6\Omega$			80		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{CE} = 600V$ $I_{C} = 200A$			170		ns
T _r	Rise Time				40		
$T_{d(off)}$	Turn-off Delay Time				450		
T_{f}	Fall Time	$R_G = 3.6\Omega$			170		İ
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$	$T_J = 25^{\circ}C$		10.4		mJ
Lon	Turn on Switching Energy	$V_{CE} = 600V$ $T_{J} = 150^{\circ}C$		21		1113	
E_{off}	Turn-off Switching Energy	$I_{\rm C} = 200 A$	$T_J = 25^{\circ}C$		11		mJ
DOII	Turn on Switching Diving	$R_G = 3.6\Omega$	$T_J = 150$ °C		18.6		1110
I_{SC}	Short circuit current	$V_{GE} \le 15V ; V_{CC} = 900V$ $t_p \le 10 \mu s ; T_i = 150 ^{\circ} C$			1000		A
R_{thJC}	Junction to Case Thermal Resistance					0.15	°C/W

CR1 to CR4 diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I_{RM}	Maximum Reverse Leakage Current	V _R =1200V	$T_i = 25^{\circ}C$ $T_i = 150^{\circ}C$			150 400	μΑ
I_{F}	DC Forward Current		$Tc = 80^{\circ}C$		180		A
17	Diada Famyand Valtaga	$I_{\rm F} = 150A$	$T_i = 25^{\circ}C$		1.7	2.2	V
V_{F}	Diode Forward Voltage	$V_{GE} = 0V$	$T_{i} = 150^{\circ}C$		1.65		V
+	Davana Pagayany Tina		$T_j = 25$ °C		155		ng
t_{rr}	Reverse Recovery Time		$T_j = 150$ °C		300		ns
Q _{rr}	Payarsa Pasayary Charga	$I_F = 150A$	$T_j = 25$ °C		14.6		μС
Qrr	Q_{rr} Reverse Recovery Charge $V_R = 600V$ $di/dt = 3800A/\mu s$	$T_{i} = 150^{\circ}C$		30.4		μС	
Б	Daviana Dagayany Enganay	αι, αι 30001 μ3	$T_j = 25$ °C		5.2		an I
E _{rr}	Reverse Recovery Energy		$T_{\rm j} = 150^{\circ}{\rm C}$		11		mJ
R_{thJC}	Junction to Case Thermal Resistance		_			0.32	°C/W

2 - 8



CR5 & CR6 diode ratings and characteristics

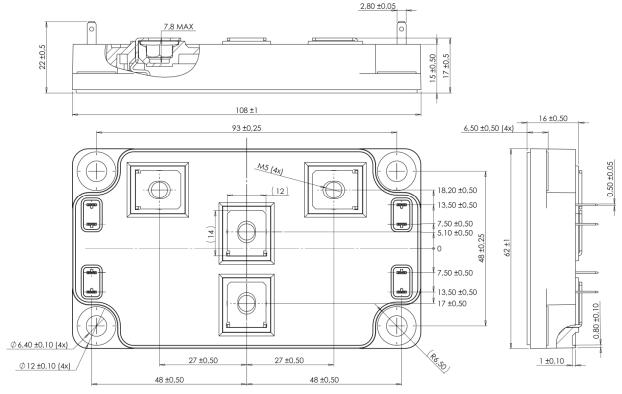
Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I_{RM}	Maximum Reverse Leakage Current	V _R =1200V	$T_i = 25$ °C $T_i = 150$ °C			150 400	μΑ
I_F	DC Forward Current		$Tc = 80^{\circ}C$		240		A
W	Diede Fernyand Voltage	$I_F = 200A$	$T_i = 25^{\circ}C$		1.9	2.4	V
V_{F}	Diode Forward Voltage	$V_{GE} = 0V$	$T_{i} = 150^{\circ}C$		1.85		V
t	Reverse Recovery Time		$T_j = 25$ °C		155		ns
t_{rr}	Reverse Recovery Time		$T_j = 150$ °C		300		115
0	Payarga Pagayary Charga	$I_{\rm F} = 200 {\rm A}$	$T_j = 25$ °C		18.6		μC
Vп	Q_{rr} Reverse Recovery Charge $V_R = 600V_{di/dt} = 4000A/\mu s$	$T_{i} = 150^{\circ}C$		39		μС	
Б	D	αν αιν 100011 μι	$T_j = 25$ °C		8.2		ana I
E _{rr}	Reverse Recovery Energy		$T_{\rm j} = 150^{\circ}{\rm C}$		16		mJ
R_{thJC}	Junction to Case Thermal Resistance					0.25	°C/W

Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
V_{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000			V
$T_{\rm J}$	Operating junction temperature range Storage Temperature Range					175	
T_{STG}						125	°C
$T_{\rm C}$	Operating Case Temperature	-40		100			
Torque	Mounting torque	To heatsink	M6	3		5	N.m
	Mounting torque	For terminals	M5	2		3.5	IN.III
Wt	Package Weight					300	g

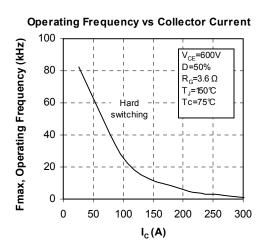


SP6 Package outline (dimensions in mm)

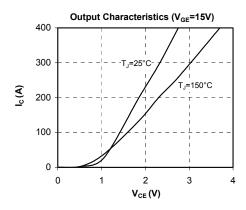


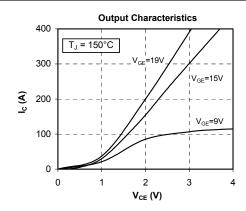
See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

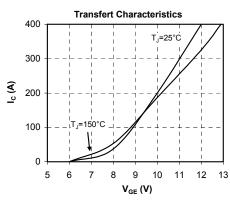
Q1 to Q4 Typical performance curve

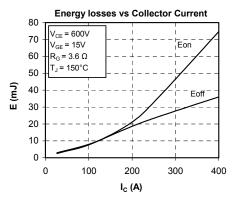


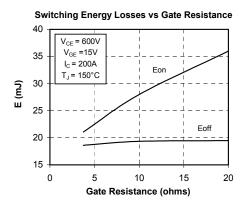


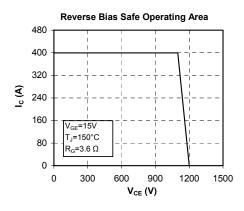


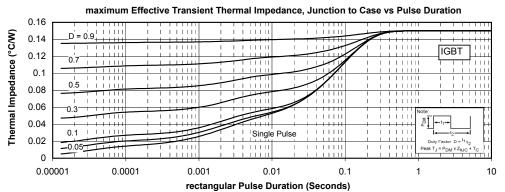






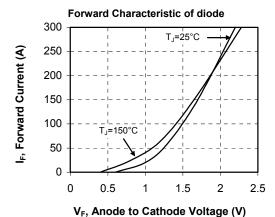




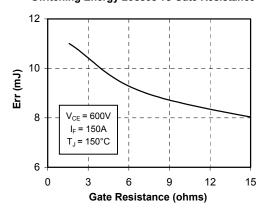


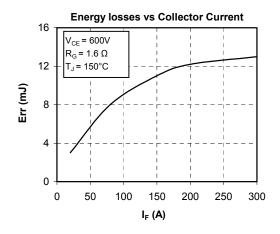


CR1 to CR4 Typical performance curve

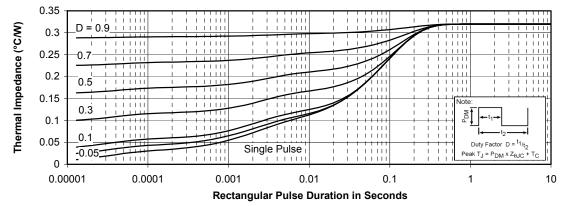


Switching Energy Losses vs Gate Resistance



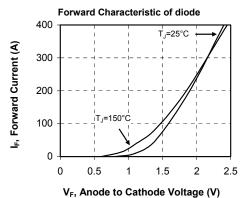


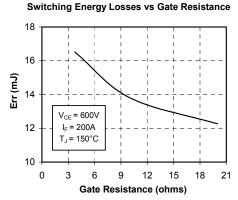
maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration

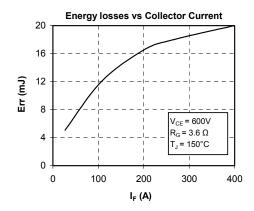




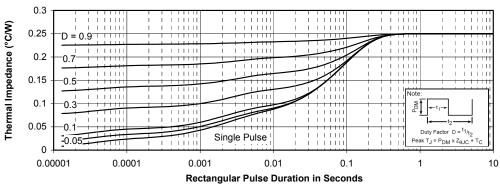
CR5 & CR6 Typical performance curve







maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration





DISCLAIMER

The information contained in the document (unless it is publicly available on the Web without access restrictions) is PROPRIETARY AND CONFIDENTIAL information of Microsemi and cannot be copied, published, uploaded, posted, transmitted, distributed or disclosed or used without the express duly signed written consent of Microsemi. If the recipient of this document has entered into a disclosure agreement with Microsemi, then the terms of such Agreement will also apply. This document and the information contained herein may not be modified, by any person other than authorized personnel of Microsemi. No license under any patent, copyright, trade secret or other intellectual property right is granted to or conferred upon you by disclosure or delivery of the information, either expressly, by implication, inducement, estoppels or otherwise. Any license under such intellectual property rights must be approved by Microsemi in writing signed by an officer of Microsemi.

Microsemi reserves the right to change the configuration, functionality and performance of its products at anytime without any notice. This product has been subject to limited testing and should not be used in conjunction with life-support or other mission-critical equipment or applications. Microsemi assumes no liability whatsoever, and Microsemi disclaims any express or implied warranty, relating to sale and/or use of Microsemi products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright or other intellectual property right. Any performance specifications believed to be reliable but are not verified and customer or user must conduct and complete all performance and other testing of this product as well as any user or customers final application. User or customer shall not rely on any data and performance specifications or parameters provided by Microsemi. It is the customer's and user's responsibility to independently determine suitability of any Microsemi product and to test and verify the same. The information contained herein is provided "AS IS, WHERE IS" and with all faults, and the entire risk associated with such information is entirely with the User. Microsemi specifically disclaims any liability of any kind including for consequential, incidental and punitive damages as well as lost profit. The product is subject to other terms and conditions which can be located on the web at http://www.microsemi.com/legal/tnc.asp

Life Support Application

Seller's Products are not designed, intended, or authorized for use as components in systems intended for space, aviation, surgical implant into the body, in other applications intended to support or sustain life, or for any other application in which the failure of the Seller's Product could create a situation where personal injury, death or property damage or loss may occur (collectively "Life Support Applications").

Buyer agrees not to use Products in any Life Support Applications and to the extent it does it shall conduct extensive testing of the Product in such applications and further agrees to indemnify and hold Seller, and its officers, employees, subsidiaries, affiliates, agents, sales representatives and distributors harmless against all claims, costs, damages and expenses, and attorneys' fees and costs arising, directly or directly, out of any claims of personal injury, death, damage or otherwise associated with the use of the goods in Life Support Applications, even if such claim includes allegations that Seller was negligent regarding the design or manufacture of the goods.

Buyer must notify Seller in writing before using Seller's Products in Life Support Applications. Seller will study with Buyer alternative solutions to meet Buyer application specification based on Sellers sales conditions applicable for the new proposed specific part.

8 - 8